

CLAIMS:

1. A semiconductor single crystal manufacturing apparatus, comprising a chamber disposed in a furnace and having a crucible in which a melt is charged, a heater for heating the crucible, and a wire disposed within the chamber, wherein:

at least a region of the wire which is exposed to a high temperature is covered with a collar.
2. The semiconductor single crystal manufacturing apparatus according to claim 1, wherein the collar is disposed in plural.
3. The semiconductor single crystal manufacturing apparatus according to claim 1 or 2, wherein the collar is disposed between a wire winding device and a seed crystal.
4. The semiconductor single crystal manufacturing apparatus according to any one of claims 1 through 3, wherein the collar is disposed closely to cover the wire.
5. A semiconductor single crystal manufacturing apparatus, comprising a chamber disposed in a furnace and having a crucible in which a melt is charged, a pull chamber disposed above the chamber, a seed holder which is vertically moved between an inside of the pull chamber and the chamber, and a wire which hangs the seed holder via a coupling member, wherein:

a length of at least either the seed holder or the coupling member is determined to be a length to locate an exposed portion of the wire near a tip end thereof in a region having a temperature less than a prescribed temperature in a high-temperature atmosphere within the furnace when a seed crystal is attached to the seed holder and located at a position to come into contact with the melt.
6. The semiconductor single crystal manufacturing apparatus according to claim 5,

wherein less than the prescribed temperature is less than 700°C.